

# Dae-Hwan Kang

## List of Publications by Year in descending order

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8  
papers

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citations

1307594

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1588992

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g-index

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docs citations

8  
times ranked

334  
citing authors

#	ARTICLE	IF	CITATIONS
1	Understanding on the current-induced crystallization process and faster set write operation thereof in non-volatile phase change memory. Applied Physics Letters, 2012, 100, 063508.	3.3	8
2	An experimental investigation on the switching reliability of a phase change memory device with an oxidized TiN electrode. Journal of Applied Physics, 2006, 100, 054506.	2.5	48
3	Switching behavior of indium selenide-based phase-change memory cell. IEEE Transactions on Magnetics, 2005, 41, 1034-1036.	2.1	53
4	Time-resolved analysis of the set process in an electrical phase-change memory device. Applied Physics Letters, 2005, 87, 253504.	3.3	27
5	Lower Voltage Operation of a Phase Change Memory Device with a Highly Resistive TiON Layer. Japanese Journal of Applied Physics, 2004, 43, 5243-5244.	1.5	34
6	Characterization of Atomic Layer Deposited $W_N$ [sub x] $C$ [sub y] Thin Film as a Diffusion Barrier for Copper Metallization. Journal of the Electrochemical Society, 2004, 151, C272.	2.9	47
7	One-dimensional heat conduction model for an electrical phase change random access memory device with an 8F2 memory cell ( $F=0.15\hat{\%}\hat{I}4m$ ). Journal of Applied Physics, 2003, 94, 3536-3542.	2.5	143
8	Atomic-layer-deposited $W_NxCy$ thin films as diffusion barrier for copper metallization. Applied Physics Letters, 2003, 82, 4486-4488.	3.3	44